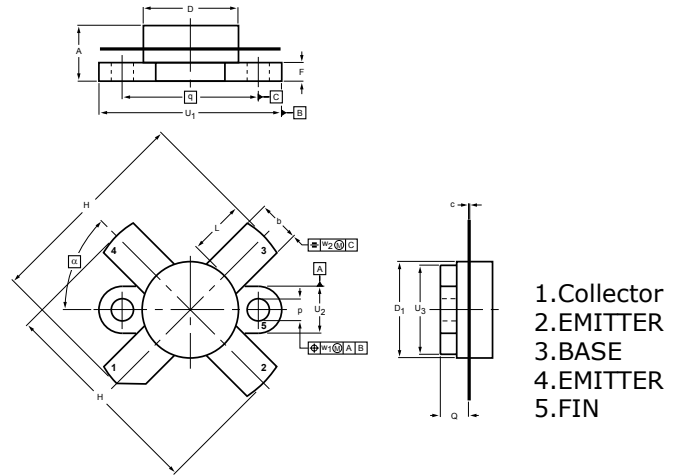


DESCRIPTION

Designed primarily for 2-30MHz SSB linear power amplifier applications (low supply voltage use)

FEATURES

- Specified 12.5V, 28MHz Characteristics
- $P_o = 150W$ PEP(Min.)
- $G_p = 10.8$ dB (Min) @28M
- Omnigold™ Metalization System



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CB0}	45	V
Collector-Emitter Voltage	V_{CES}	45	V
Collector-Emitter Voltage	V_{CEO}	18	V
Collector Current	I_C	35	A
Emitter-Base Voltage	V_{EBO}	4.5	V
Collector Power Dissipation	P_{DISS}	360	W
Junction Temperature	T_J	-65 to 175	°C
Storage Temperature Range	T_{STG}	-65 to 175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=100mA, I_B=0$	18	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=100mA, V_{EB}=0$	45	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	4.5	-	-	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 30V, I_E = 0$	-	-	500	μA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=10A$	10	-	150	
Power Gain	G_p	$V_{CC}=12.5V, P_{OUT}=150W, f=28MHz, P_{IN}=6.5W$	10.8	-	-	dB
Collector Efficiency	η_c		35	-	-	%
Intermodulation Distortion	IMD		-	-	-18	dB
Collector Output Capacitance	C_{ob}	$V_{CB}=12.5V, I_E=0, f=1MHz$	-	-	720	pF

Note : Above parameters , ratings , limits and conditions are subject to change.